

CD4020BMS, CD4024BMS, CD4040BMS

CMOS Ripple-Carry Binary Counter/Dividers

October 1996

Features

- High Voltage Types (20V Rating)
- Medium Speed Operation
- Fully Static Operation
- · Buffered Inputs and Outputs
- 100% Tested for Quiescent Current at 20V
- Standardized Symmetrical Output Characteristics
- Common Reset
- 5V, 10V and 15V Parametric Ratings
- Maximum Input Current of 1µa at 18V Over Full Package-Temperature Range;
 - 100nA at 18V and 25°C
- Noise Margin (Over Full Package Temperature Range):
 - 1V at VDD = 5V
 - 2V at VDD = 10V
 - 2.5V at VDD = 15V
- Meets All Requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications For Description Of 'B' Series CMOS Devices"

Applications

- Control Counters
- Timers
- Frequency Dividers
- Time-Delay Circuits

Description

CD4020BMS - 14 Stage

CD4024BMS - 7 Stage

CD4040BMS - 12 Stage

CD4020BMS, CD4024BMS, and CD4040BMS are ripple-carry binary counters. All counter stages are master-slave flip-flops. The state of a counter advances one count on the negative transition of each input pulse; a high level on the RESET line resets the counter to its all zeros state. Schmitt trigger action on the input-pulse line permits unlimited rise and fall times. All inputs and outputs are buffered.

The CD4020BMS, CD4024BMS and the CD4040BMS is supplied in these 14 lead outline packages:

	CD4020B	CD4024B	CD4040B
Braze Seal DIP	H4W	H4Q	H4X
Frit Seal DIP	H1F	H1B	H1F
Ceramic Flatpack	H6W	H3W	H6W

Pinouts CD4020BMS TOP VIEW Q12 1 16 VDD 15 Q11 Q13 2 14 Q10 Q14 3 13 Q8 Q6 4 12 Q9 Q5 5 Q7 6 11 RESET Q4 7 **10** θ VSS 8 9 Q1 **CD4024BMS TOP VIEW** θ 1 14 VDD RESET 2 13 NC 12 Q1 11 Q2 10 NC Q5 5 Q4 6 9 Q3 vss 7 8 NC NC = NO CONNECTION **CD4040BMS** TOP VIEW 16 VDD Q12 1 15 Q11 Q6 2 Q5 3 14 Q10 13 Q8 Q7 4 12 Q9 Q4 5 11 R Q3 6 Q2 7 **10** θ vss 8 9 Q1

Absolute Maximum Ratings Reliability Information Ceramic DIP and FRIT Package θ_{ja} Clathack Package 80°C/W $^{ heta_{jc}}$ 20°C/W DC Supply Voltage Range, (VDD) -0.5V to +20V (Voltage Referenced to VSS Terminals) Input Voltage Range, All Inputs -0.5V to VDD +0.5V Flatpack Package 70°C/W 20°C/W DC Input Current, Any One Input.....±10mA Maximum Package Power Dissipation (PD) at +125°C Operating Temperature Range -55°C to +125°C For TA = -55° C to $+100^{\circ}$ C (Package Type D, F, K) 500mW Package Types D, F, K, H For TA = +100°C to +125°C (Package Type D, F, K) Derate Storage Temperature Range (TSTG) -65°C to +150°C Linearity at 12mW/°C to 200mW Lead Temperature (During Soldering) +265°C Device Dissipation per Output Transistor 100mW

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

				GROUP A		LIN	IITS	
PARAMETER	SYMBOL	CONDITIONS (I	NOTE 1)	SUBGROUPS	TEMPERATURE	MIN	MAX	UNITS
Supply Current	IDD	VDD = 20V, VIN = VD	D or GND	1	+25°C	-	10	μΑ
				2	+125°C	-	1000	μΑ
		VDD = 18V, VIN = VD	D or GND	3	-55°C	-	10	μΑ
Input Leakage Current	IIL	VIN = VDD or GND	/IN = VDD or GND VDD = 20		+25°C	-100	-	nA
				2	+125°C	-1000	-	nA
			VDD = 18V	3	-55°C	-100	-	nA
Input Leakage Current	IIH	VIN = VDD or GND	VDD = 20	1	+25°C	-	100	nA
				2	+125°C	-	1000	nA
			VDD = 18V	3	-55°C	-	100	nA
Output Voltage	VOL15	VDD = 15V, No Load	-	1, 2, 3	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOH15	VDD = 15V, No Load	(Note 3)	1, 2, 3	+25°C, +125°C, -55°C	14.95	-	V
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.	.4V	1	+25°C	0.53	-	mA
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0	0.5V	1	+25°C	1.4	-	mA
Output Current (Sink)	IOL15	VDD = 15V, VOUT =	VDD = 15V, VOUT = 1.5V		+25°C	3.5	-	mA
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V		1	+25°C	-	-0.53	mA
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.	5V	1	+25°C	-	-1.8	mA
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9	9.5V	1	+25°C	-	-1.4	mA
Output Current (Source)	IOH15	VDD = 15V, VOUT =	13.5V	1	+25°C	-	-3.5	mA
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10	μΑ	1	+25°C	-2.8	-0.7	V
P Threshold Voltage	VPTH	VSS = 0V, IDD = 10μ/	4	1	+25°C	0.7	2.8	V
Functional	F	VDD = 2.8V, VIN = VI	DD or GND	7	+25°C	VOH>	VOL <	V
		VDD = 20V, VIN = VD	D or GND	7	+25°C	VDD/2	VDD/2	
		VDD = 18V, VIN = VD	D or GND	8A	+125°C			
		VDD = 3V, VIN = VDD	or GND	8B	-55°C			
Input Voltage Low (Note 2)	VIL	VDD = 5V, VOH > 4.5V, VOL < 0.5V		1, 2, 3	+25°C, +125°C, -55°C	-	1.5	V
Input Voltage High (Note 2)	VIH	VDD = 5V, VOH > 4.5V, VOL < 0.5V		1, 2, 3	+25°C, +125°C, -55°C	3.5	-	V
Input Voltage Low (Note 2)	VIL	VDD = 15V, VOH > 13.5V, VOL < 1.5V		1, 2, 3	+25°C, +125°C, -55°C	-	4	V
Input Voltage High (Note 2)	VIH	VDD = 15V, VOH > 13 VOL < 1.5V	3.5V,	1, 2, 3	+25°C, +125°C, -55°C	11	-	V

NOTES: 1. All voltages referenced to device GND, 100% testing being 3. For accuracy, voltage is measured differentially to VDD. Limit implemented.

At Distance 1/16 \pm 1/32 Inch (1.59mm \pm 0.79mm) from case for

10s Maximum

is 0.050V max.

For TA = Full Package Temperature Range (All Package Types)

2. Go/No Go test with limits applied to inputs

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

			GROUP A		LIM	IITS	
PARAMETER	SYMBOL	CONDITIONS (NOTE 1, 2)	SUBGROUPS	TEMPERATURE	MIN	MAX	UNITS
Propagation Delay	TPHL1	VDD = 5V, VIN = VDD or GND	9	+25°C	-	360	ns
0 To Q1	TPLH1		10, 11	+125°C, -55°C	-	486	ns
Propagation Delay	TPHL2	VDD = 5V, VIN = VDD or GND	9	+25°C	-	330	ns
Qn To Qn + 1	TPLH2		10, 11	+125°C, -55°C	-	446	ns
Propagation Delay	TPLH3	VDD = 5V, VIN = VDD or GND	9	+25°C	-	280	ns
Reset To Q	TPHL3		10, 11	+125°C, -55°C	-	378	ns
Transition Time	TTHL	VDD = 5V, VIN = VDD or GND	9	+25°C	-	200	ns
Q1	TTLH		10, 11	+125°C, -55°C	-	270	ns
Maximum Clock Input	FCL	VDD = 5V, VIN = VDD or GND	9	+25°C	3.5	-	MHz
Frequency			10, 11	+125°C, -55°C	2.22	-	MHz

NOTES:

- 1. VDD = 5V, CL = 50pF, RL = 200K
- 2. -55°C and +125°C limits guaranteed, 100% testing being implemented.

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

			_		LIN	IITS	
PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	MAX	UNITS
Supply Current	IDD	VDD = 5V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	5	μΑ
				+125°C	-	150	μΑ
		VDD = 10V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	10	μΑ
				+125°C	-	300	μΑ
		VDD = 15V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	10	μΑ
				+125°C	-	600	μΑ
Output Voltage	VOL	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOL	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOH	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	4.95	-	V
Output Voltage	VOH	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	9.95	-	V
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.4V	1, 2	+125°C	0.36	-	mA
				-55°C	0.64	-	mA
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V	1, 2	+125°C	0.9	-	mA
				-55°C	1.6	-	mA
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1.5V	1, 2	+125°C	2.4	-	mA
				-55°C	4.2	-	mA
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V	1, 2	+125°C	-	-0.36	mA
				-55°C	-	-0.64	mA
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.5V	1, 2	+125°C	-	-1.15	mA
				-55°C	-	-2.0	mA
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9.5V	1, 2	+125°C	-	-0.9	mA
				-55°C	-	-1.6	mA
Output Current (Source)	IOH15	VDD =15V, VOUT = 13.5V	1, 2	+125°C	-	-2.4	mA
				-55°C	-	-4.2	mA

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

					LIMITS		
PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	MAX	UNITS
Input Voltage Low	put Voltage Low VIL VDD = 10\		1, 2	+25°C, +125°C, -55°C	-	3	V
Input Voltage High	VIH	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	7	-	V
Propagation Delay	TPHL1	VDD = 10V	1, 2, 3	+25°C	-	160	ns
Input To Q1	TPLH1	VDD = 15V	1, 2, 3	+25°C	-	130	ns
Propagation Delay	TPHL2	VDD = 10V	1, 2, 3	+25°C	-	80	ns
QN To QN + 1	TPLH2	VDD = 15V	1, 2, 3	+25°C	-	60	ns
Propagation Delay	TPHL3	VDD = 10V	1, 2, 3	+25°C	-	120	ns
Reset To Q		VDD = 15V	1, 2, 3	+25°C	-	100	ns
Transition Time	TTHL	VDD = 10V	2, 3	+25°C	-	100	ns
	TTLH	VDD = 15V	2, 3	+25°C	-	80	ns
Maximum Clock Input	FCL	VDD = 10V	1, 2, 3	+25°C	8	-	MHz
Frequency		VDD = 15V	1, 2, 3	+25°C	12	-	MHz
Minimum Reset Pulse	TW	VDD = 5V	1, 2, 3	+25°C	-	200	ns
Width		VDD = 10V	1, 2, 3	+25°C	-	80	ns
		VDD = 15V	1, 2, 3	+25°C	-	60	ns
Reset Removal Time	TREM	VDD = 5V	1, 2, 3	+25°C	-	350	ns
		VDD = 10V	1, 2, 3	+25°C	-	150	ns
		VDD = 15V	1, 2, 3	+25°C	-	100	ns
Minimum Input Pulse	TW	VDD = 5V	1, 2, 3	+25°C	-	140	ns
Width		VDD = 10V	1, 2, 3	+25°C	-	60	ns
		VDD = 15V	1, 2, 3	+25°C	-	40	ns
Input Capacitance	CIN	Any Input	1, 2	+25°C	-	7.5	pF

NOTES:

- 1. All voltages referenced to device GND.
- 2. The parameters listed on Table 3 are controlled via design or process and are not directly tested. These parameters are characterized on initial design release and upon design changes which would affect these characteristics.
- 3. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

TABLE 4. POST IRRADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS

					LIM	IITS	
PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	MAX	UNITS
Supply Current	IDD	VDD = 20V, VIN = VDD or GND	1, 4	+25°C	-	25	μΑ
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10μA	1, 4	+25°C	-2.8	-0.2	V
N Threshold Voltage Delta	ΔVTND	VDD = 10V, ISS = -10μA	1, 4	+25°C	-	±1	V
P Threshold Voltage	VTP	VSS = 0V, IDD = 10μA	1, 4	+25°C	0.2	2.8	V
P Threshold Voltage Delta	ΔVTPD	VSS = 0V, IDD = 10μA	1, 4	+25°C	-	±1	V
Functional	F	VDD = 18V, VIN = VDD or GND	1	+25°C	VOH >	VOL <	V
		VDD = 3V, VIN = VDD or GND			VDD/2	VDD/2	
Propagation Delay Time	TPHL TPLH	VDD = 5V	1, 2, 3, 4	+25°C	-	1.35 x +25°C Limit	ns

TABLE 4. POST IRRADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

ı						LIM	ITS		
	PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	MAX	UNITS	

NOTES: 1. All voltages referenced to device GND.

2. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

3. See Table 2 for +25°C limit.

4. Read and Record

TABLE 5. BURN-IN AND LIFE TEST DELTA PARAMETERS +25°C

PARAMETER	SYMBOL	DELTA LIMIT
Supply Current - MSI-2	IDD	± 1.0μA
Output Current (Sink)	IOL5	± 20% x Pre-Test Reading
Output Current (Source)	IOH5A	± 20% x Pre-Test Reading

TABLE 6. APPLICABLE SUBGROUPS

CONFOR	RMANCE GROUP	MIL-STD-883 METHOD	GROUP A SUBGROUPS	READ AND RECORD
Initial Test (P	re Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test 1	(Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test 2	(Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note	1)	100% 5004	1, 7, 9, Deltas	
Interim Test 3	(Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note	1)	100% 5004	1, 7, 9, Deltas	
Final Test		100% 5004	2, 3, 8A, 8B, 10, 11	
Group A		Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11	
Group B	Subgroup B-5	Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11, Deltas	Subgroups 1, 2, 3, 9, 10, 11
Subgroup B-6		Sample 5005	1, 7, 9	
Group D		Sample 5005	1, 2, 3, 8A, 8B, 9	Subgroups 1, 2 3

NOTE: 1.5% Parameteric, 3% Functional; Cumulative for Static 1 and 2.

TABLE 7. TOTAL DOSE IRRADIATION

	MIL-STD-883		TEST		RECORD
CONFORMANCE GROUPS	METHOD	PRE-IRRAD POST-IRRAD		PRE-IRRAD	POST-IRRAD
Group E Subgroup 2	5005	1, 7, 9	Table 4	1, 9	Table 4

TABLE 8. BURN-IN AND IRRADIATION TEST CONNECTIONS

					OSCILL	.ATOR
FUNCTION	OPEN	GROUND	VDD	9V ± -0.5V	50kHz	25kHz
PART NUMBER	CD4020BMS				•	
Static Burn-In 1 Note 1	1 - 7, 9, 12 - 15	8, 10, 11	16			
Static Burn-In 2 Note 1	1 - 7, 9, 12 - 15	8	10, 11, 16			
Dynamic Burn- In Note 1	-	8, 11	16	1 - 7, 9, 12 - 15	10	
Irradiation Note 2	1 - 7, 9, 12 - 15	8	10, 11, 16			
PART NUMBER	CD4024BMS			•	•	
Static Burn-In 1 Note 1	3 - 6, 8 - 13	1, 2, 7	14			

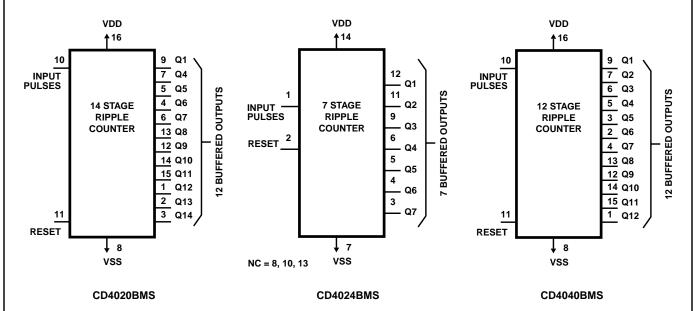
TABLE 8. BURN-IN AND IRRADIATION TEST CONNECTIONS (Continued)

					OSCIL	LATOR
FUNCTION	OPEN	GROUND	VDD	9V ± -0.5V	50kHz	25kHz
Static Burn-In 2 Note 1	3 - 6, 8 - 13	7	1, 2, 14			
Dynamic Burn- In Note 1	8, 10, 13	2, 7	14	3 - 6, 9, 11, 12	1	
Irradiation Note 2	3 - 6, 8 - 13	7	1, 2, 14			
PART NUMBER	CD4040BMS		•			•
Static Burn-In 1 Note 1	1 - 7, 9, 12 - 15	8, 10, 11	16			
Static Burn-In 2 Note 1	1 - 7, 9, 12 - 15	8	10, 11, 16			
Dynamic Burn- In Note 1	-	8, 11	16	1 - 7, 9, 12 - 15	10	
Irradiation Note 2	1 - 7, 9, 12 - 15	8	10, 11, 16			

NOTE:

- 1. Each pin except VDD and GND will have a series resistor of 10K \pm 5%, VDD = 18V \pm 0.5V
- 2. Each pin except VDD and GND will have a series resistor of 47K \pm 5%; Group E, Subgroup 2, sample size is 4 dice/wafer, 0 failures, VDD = $10V \pm 0.5V$

Functional Diagrams



Logic Diagrams

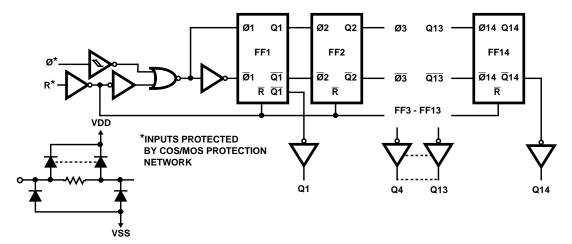


FIGURE 1. LOGIC DIAGRAM FOR CD4020BMS

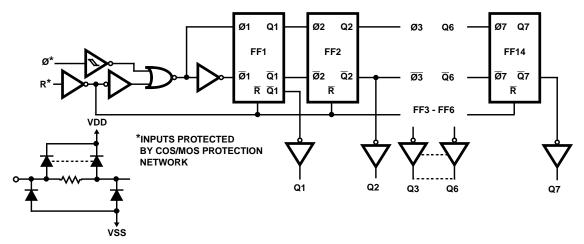


FIGURE 2. LOGIC DIAGRAM FOR CD4024BMS

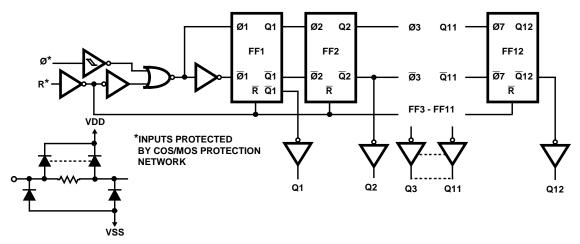


FIGURE 3. LOGIC DIAGRAM FOR CD4040BMS

Typical Performance Characteristics

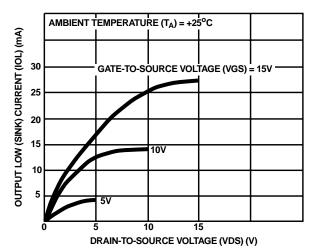


FIGURE 4. TYPICAL OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

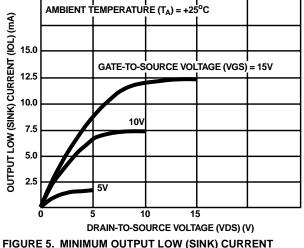


FIGURE 5. MINIMUM OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

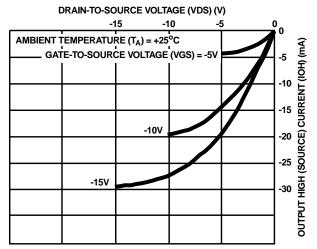


FIGURE 6. TYPICAL OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

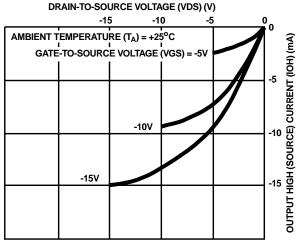


FIGURE 7. MINIMUM OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

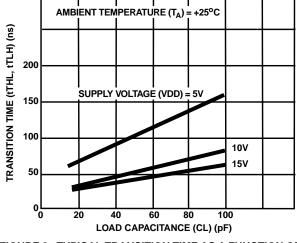


FIGURE 8. TYPICAL TRANSITION TIME AS A FUNCTION OF LOAD CAPACITANCE

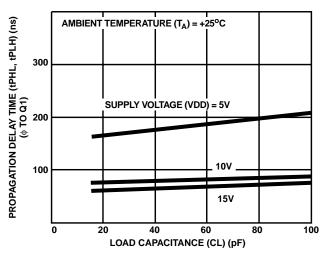
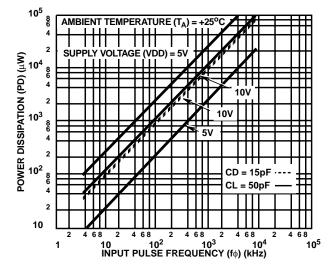
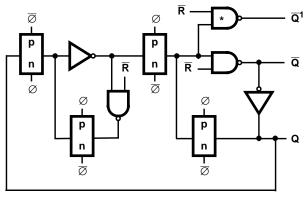


FIGURE 9. TYPICAL PROPAGATION DELAY TIME AS A FUNCTION OF LOAD CAPACITANCE (\$\phi\$ TO Q1))

CD4020BMS, CD4024BMS, CD4040BMS

Typical Performance Characteristics (Continued)



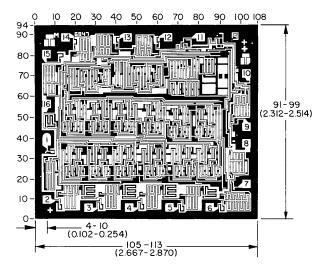


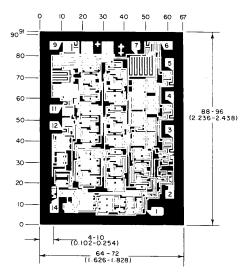
* ON FIRST STAGE ONLY

FIGURE 10. TYPICAL DYNAMIC POWER DISSIPATION AS A FUNCTION OF INPUT PULSE FREQUENCY FOR CD4020BMS

FIGURE 11. DETAIL OF TYPICAL FLIP-FLOP STAGES

Chip Dimensions and Pad Layouts





Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10⁻³ inch)

DIMENSIONS AND PAD LAYOUT FOR CD4020BMS. DIMENSIONS AND PAD LAYOUT FOR CD4040BMS ARE IDENTICAL

DIMENSIONS AND PAD LAYOUT FOR CD4024BMSH

METALLIZATION: Thickness: 11kÅ - 14kÅ, AL.

PASSIVATION: 10.4kÅ - 15.6kÅ, Silane

BOND PADS: 0.004 inches X 0.004 inches MIN **DIE THICKNESS:** 0.0198 inches - 0.0218 inches

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